





**TM07N02I**

**N-Channel Enhancement Mosfet**

**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$  unless otherwise specified)

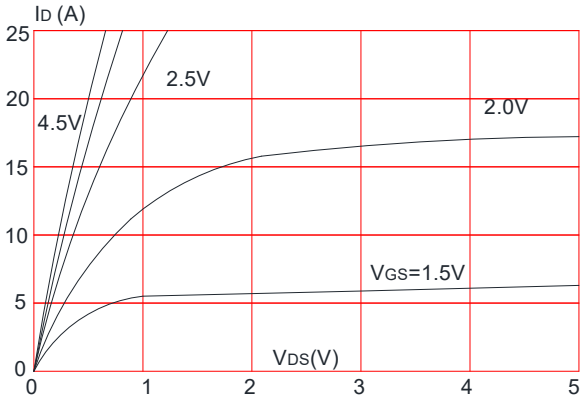
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1.0	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4	0.7	1	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	$V_{GS}=4.5V, I_D=4A$	-	16	24	m $\Omega$
		$V_{GS}=2.5V, I_D=3A$	-	25	40	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=10V, V_{GS}=0V,$ $f=1.0MHz$	-	358	-	pF
$C_{oss}$	Output Capacitance		-	69.3	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	58.5	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=10V, I_D=2A,$ $V_{GS}=4.5V$	-	5.6	-	nC
$Q_{gs}$	Gate-Source Charge		-	0.8	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	1	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10V,$ $I_D=4A, R_{GEN}=3\Omega,$ $V_{GS}=4.5V$	-	5	-	ns
$t_r$	Turn-on Rise Time		-	30	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	48	-	ns
$t_f$	Turn-off Fall Time		-	36	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	6.8	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	25	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=4A$	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

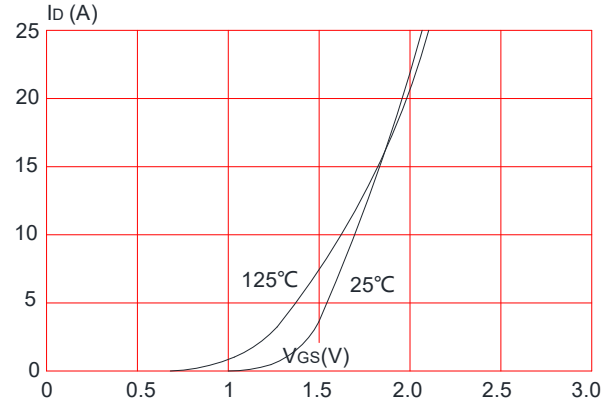
2. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

### Typical Performance Characteristics

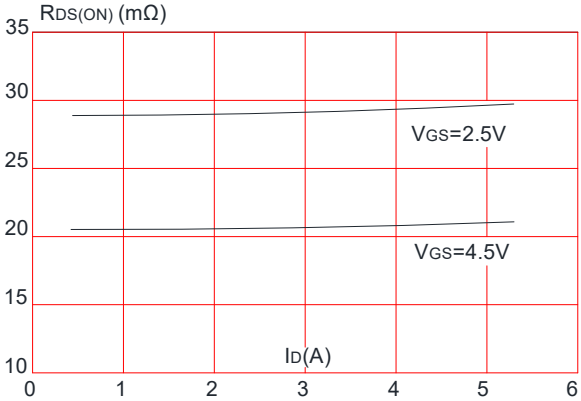
**Figure 1: Output Characteristics**



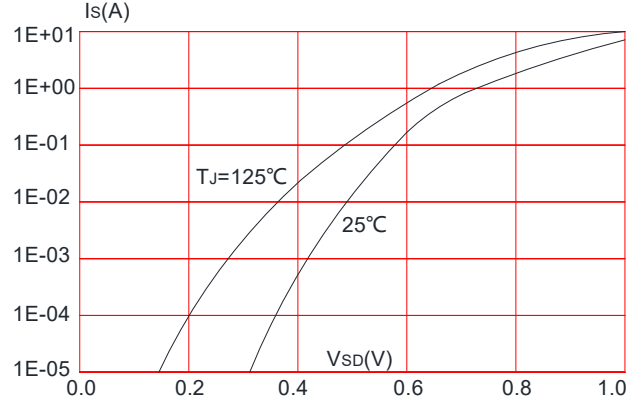
**Figure 2: Typical Transfer Characteristics**



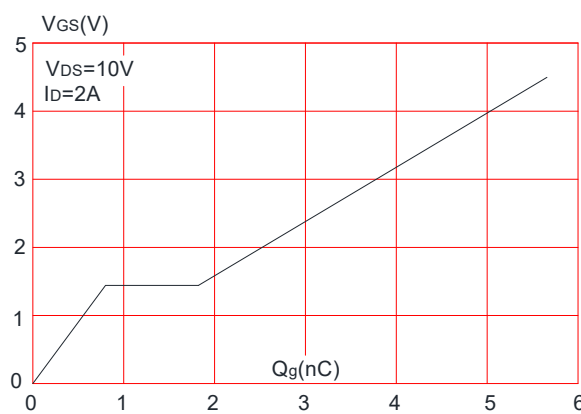
**Figure 3: On-resistance vs. Drain Current**



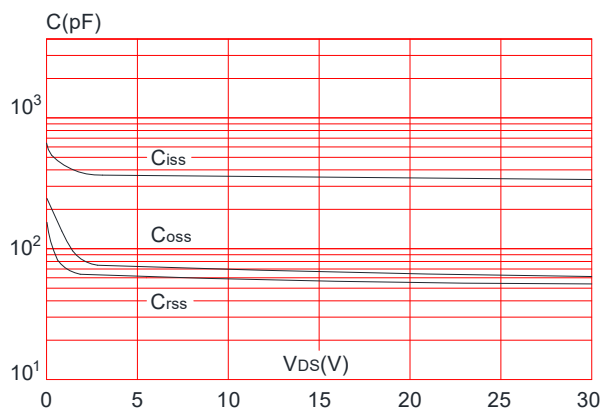
**Figure 4: Body Diode Characteristics**



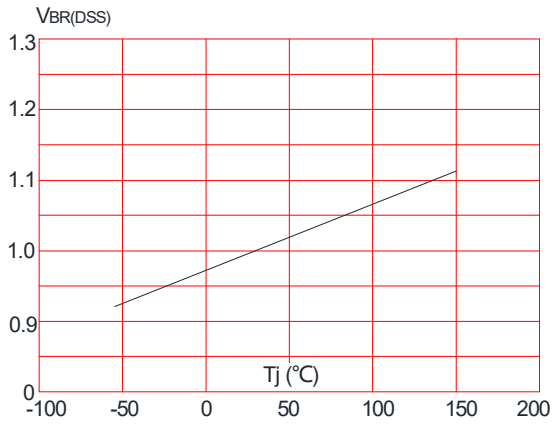
**Figure 5: Gate Charge Characteristics**



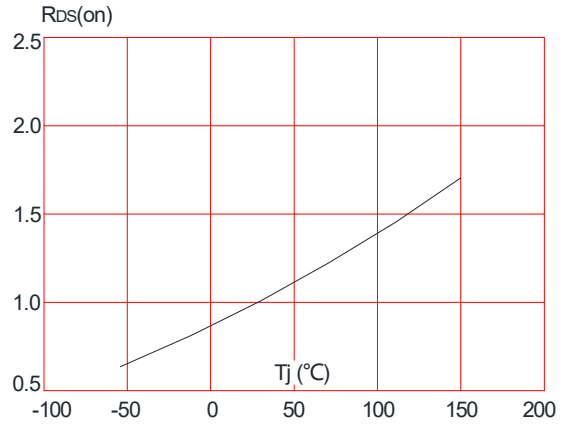
**Figure 6: Capacitance Characteristics**



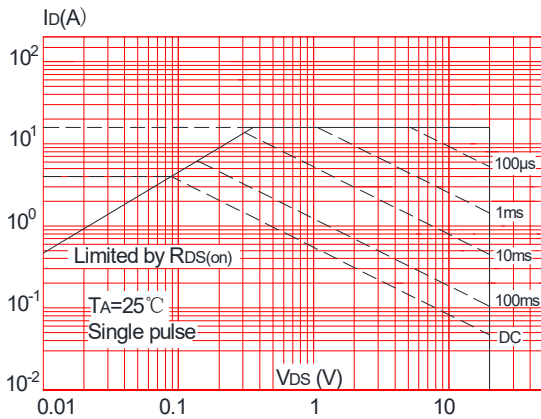
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



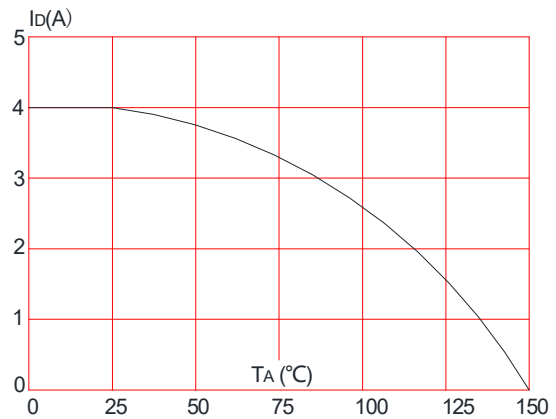
**Figure 8:** Normalized on Resistance vs. Junction Temperature



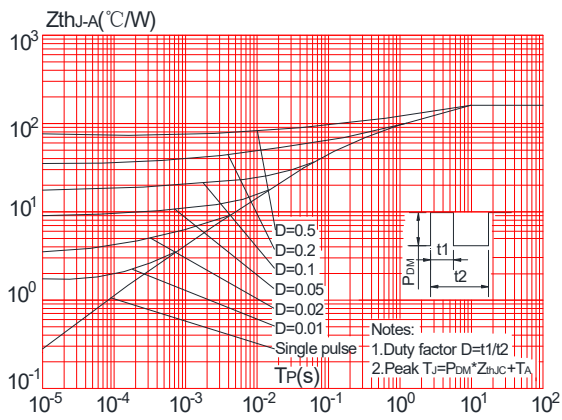
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



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